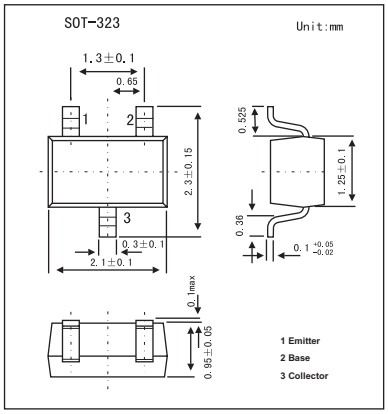
TY Semicondutor®

Product specification

2SC4666



■ Features

- High h_{FE}: h_{FE} = 600～3600
- High voltage: V_{CEO} = 50 V
- High collector current: I_C = 150 mA (max)
- Small package

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	150	mA
Base current	I_B	30	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 50 V, I_E = 0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 5 V, I_C = 0			0.1	μA
DC current gain	h_{FE}	V_{CE} = 6 V, I_C = 2 mA	600		3600	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = 100 mA, I_B = 10 mA		0.12	0.25	V
Transition frequency	f_T	V_{CE} = 10 V, I_C = 10 mA	100	250		MHz
Collector output capacitance	C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz		3.5		pF
Noise figure	NF(1)	V_{CE} = 6 V, I_C = 0.1 mA, f = 100 Hz,Rg = 10 kΩ		0.5		dB
	NF(2)	V_{CE} = 6 V, I_C = 0.1 mA, f = 1 kHz,Rg = 10 kΩ		0.3		dB

■ h_{FE} Classification

Marking	P	
Rank	A	B
hFE	600～1800	1200～3600